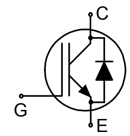
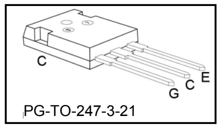
SKW30N60HS

High Speed IGBT in NPT-technology





- 30% lower E_{off} compared to previous generation
- Short circuit withstand time – 10 µs
- Designed for operation above 30 kHz
- NPT-Technology for 600V applications offers:
  - parallel switching capability
  - moderate E_{off} increase with temperature
  - very tight parameter distribution

- High ruggedness, temperature stable behaviour
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC[1] for target applications
- Complete product spectrum and PSpice Models : http://www.infineon.com/igbt/

Type	V_{CE}	I_C	E_{off}	T_j	Marking	Package
SKW30N60HS	600V	30	480µJ	150°C	K30N60HS	PG-TO-247-3-21

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	600	V
DC collector current T_C = 25°C T_C = 100°C	I_C	 41 30	A
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	112	
Turn off safe operating area $V_{CE} \leq 600V$, $T_j \leq 150°C$	-	112	
Diode forward current T_C = 25°C T_C = 100°C	I_F	 41 28	
Diode pulsed current, t_p limited by T_{jmax}	I_{Fpuls}	112	
Gate-emitter voltage static transient (t_p<1µs, D<0.05)	V_{GE}	±20 ±30	V
Short circuit withstand time[2)] V_{GE} = 15V, $V_{CC} \leq 600V$, $T_j \leq 150°C$	t_{SC}	10	µs
Power dissipation T_C = 25°C	P_{tot}	250	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C
Time limited operating junction temperature for t < 150h	$T_{j(tl)}$	175	
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

[1] J-STD-020 and JESD-022
[2)] Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		0.5	K/W
Diode thermal resistance, junction – case	R_{thJCD}		1.29	
Thermal resistance, junction – ambient	R_{thJA}		40	

Electrical Characteristic, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE}=0V, I_C=500µA	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE} = 15V, I_C=30A T_j=25°C T_j=150°C		 2.8 3.5	 3.15 4.00	
Diode forward voltage	V_F	V_{GE}=0V, I_F=30A T_j=25°C T_j=150°C	 -	 1.55 1.55	 2.05 2.05	
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C=700µA, V_{CE}=V_{GE}	3	4	5	
Zero gate voltage collector current	I_{CES}	V_{CE}=600V, V_{GE}=0V T_j=25°C T_j=150°C	 - -	 - -	 40 3000	µA
Gate-emitter leakage current	I_{GES}	V_{CE}=0V, V_{GE}=20V	-	-	100	nA
Transconductance	g_{fs}	V_{CE}=20V, I_C=30A	-	20		S

Dynamic Characteristic

Parameter	Symbol	Conditions	min.	Typ.	max.	Unit
Input capacitance	C_{iss}	V_{CE}=25V,	-	1500		pF
Output capacitance	C_{oss}	V_{GE}=0V,	-	203		
Reverse transfer capacitance	C_{rss}	f=1MHz	-	92		
Gate charge	Q_{Gate}	V_{CC}=480V, I_C=30A V_{GE}=15V	-	141		nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13		nH
Short circuit collector current[1)]	$I_{C(SC)}$	V_{GE}=15V, t_{SC}≤10µs V_{CC} ≤ 600V, T_j ≤ 150°C	-	220		A

[1)] Allowed number of short circuits: <1000; time between short circuits: >1s.

Switching Characteristic, Inductive Load, at T_j=25 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=25°C, V_{CC}=400V, I_C=30A, V_{GE}=0/15V, R_G=11Ω, L_σ[2] =60nH, C_σ[2] =40pF Energy losses include "tail" and diode reverse recovery.	-	20		ns
Rise time	t_r		-	21		
Turn-off delay time	$t_{d(off)}$		-	250		
Fall time	t_f		-	25		
Turn-on energy	E_{on}		-	0.60		mJ
Turn-off energy	E_{off}		-	0.55		
Total switching energy	E_{ts}		-	1.15		

Anti-Parallel Diode Characteristic

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Diode reverse recovery time	t_{rr} t_S t_F	T_j=25°C, V_R=400V, I_F=30A, di_F/dt=1100A/µs	- - -	125 20 105		ns
Diode reverse recovery charge	Q_{rr}		-	0.82		µC
Diode peak reverse recovery current	I_{rrm}		-	17		A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	580		A/µs

[2] Leakage inductance L_σ and Stray capacity C_σ due to test circuit in Figure E.

Switching Characteristic, Inductive Load, at T_j=150 °C

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	T_j=150°C V_{CC}=400V, I_C=30A, V_{GE}=0/15V, R_G= 1.8Ω L_σ[1)] =60nH, C_σ[1)] =40pF Energy losses include "tail" and diode reverse recovery.	-	16		ns
Rise time	t_r		-	13		
Turn-off delay time	$t_{d(off)}$		-	122		
Fall time	t_f		-	29		
Turn-on energy	E_{on}		-	0.78		mJ
Turn-off energy	E_{off}		-	0.48		
Total switching energy	E_{ts}		-	1.26		
Turn-on delay time	$t_{d(on)}$	T_j=150°C V_{CC}=400V, I_C=30A, V_{GE}=0/15V, R_G= 11Ω L_σ[1)] =60nH, C_σ[1)] =40pF Energy losses include "tail" and diode reverse recovery.	-	20		ns
Rise time	t_r		-	19		
Turn-off delay time	$t_{d(off)}$		-	274		
Fall time	t_f		-	27		
Turn-on energy	E_{on}		-	0.91		mJ
Turn-off energy	E_{off}		-	0.70		
Total switching energy	E_{ts}		-	1.61		

Anti-Parallel Diode Characteristic

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Diode reverse recovery time	t_{rr} t_S t_F	T_j=150°C V_R=400V, I_F=30A, di_F/dt=1250A/µs	- - -	190 30 160		ns
Diode reverse recovery charge	Q_{rr}		-	2.0		µC
Diode peak reverse recovery current	I_{rrm}		-	24		A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	480		A/µs

1) Leakage inductance L_σ and Stray capacity C_σ due to test circuit in Figure E.

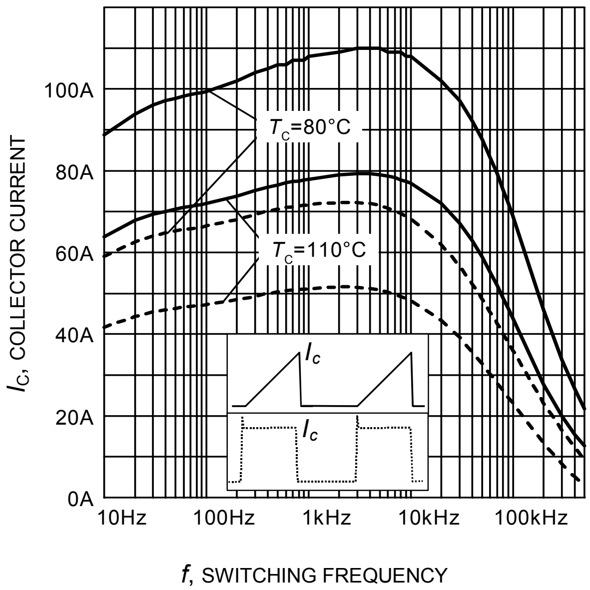


Figure 1. Collector current as a function of switching frequency
($T_j \leq 150°C$, D = 0.5, V_{CE} = 400V, V_{GE} = 0/+15V, R_G = 11Ω)

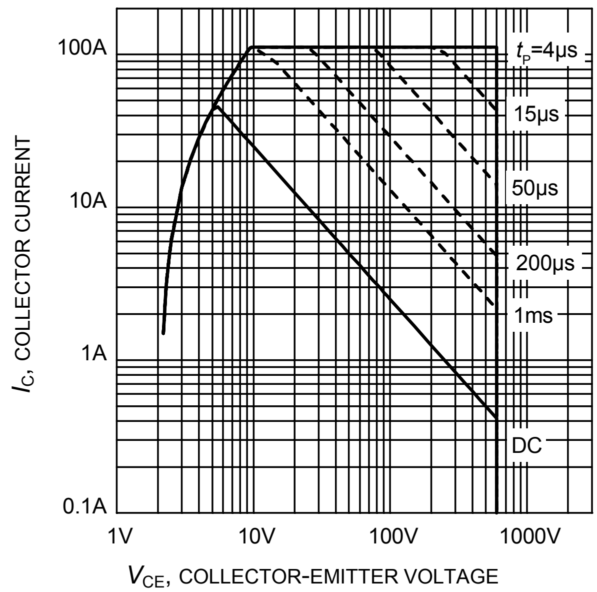


Figure 2. Safe operating area
(D = 0, T_C = 25°C, $T_j \leq 150°C$; V_{GE}=15V)

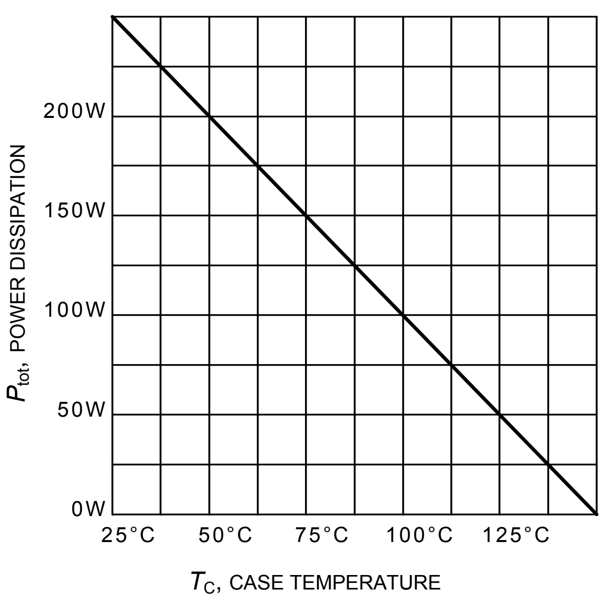


Figure 3. Power dissipation as a function of case temperature
($T_j \leq 150°C$)

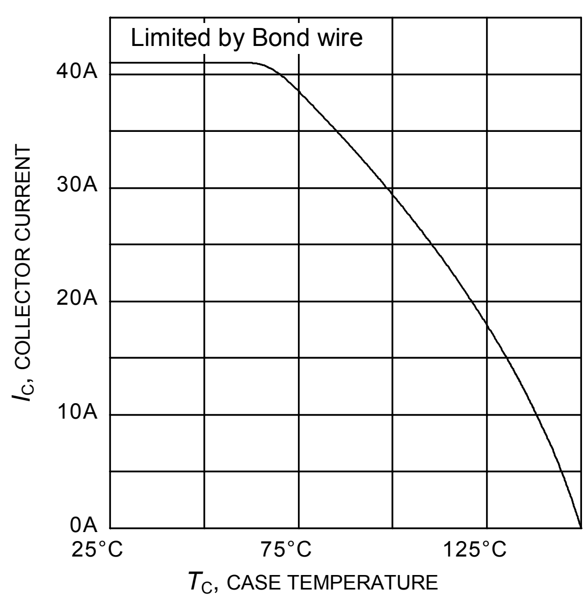


Figure 4. Collector current as a function of case temperature
($V_{GE} \leq 15V$, $T_j \leq 150°C$)

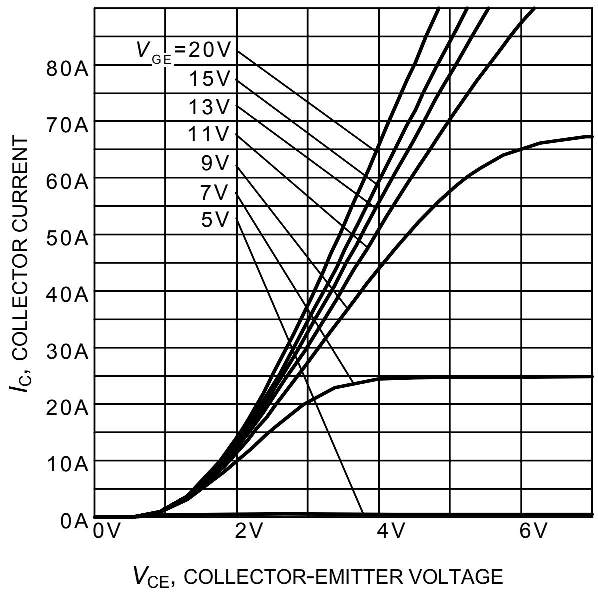


Figure 5. Typical output characteristic
(T_j = 25°C)

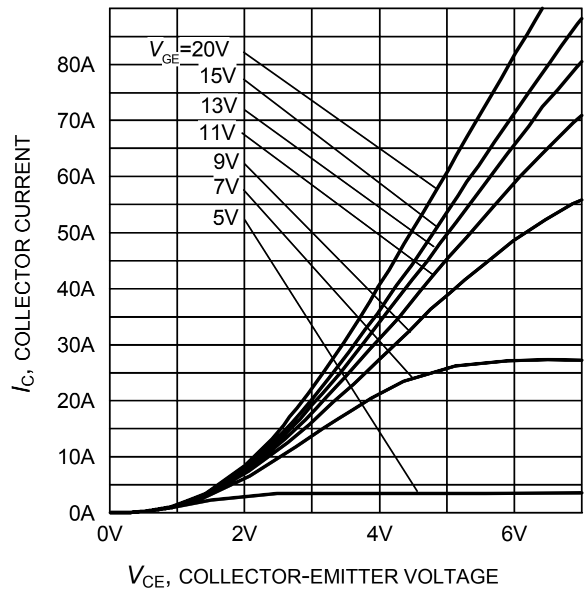


Figure 6. Typical output characteristic
(T_j = 150°C)

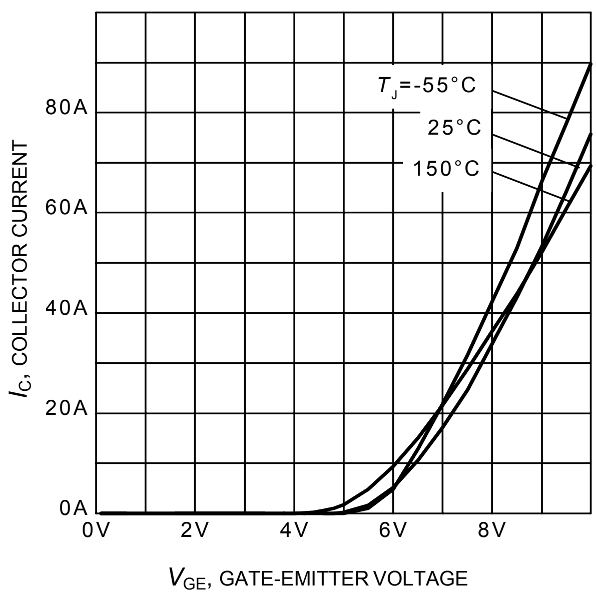


Figure 7. Typical transfer characteristic
(V_{CE}=10V)

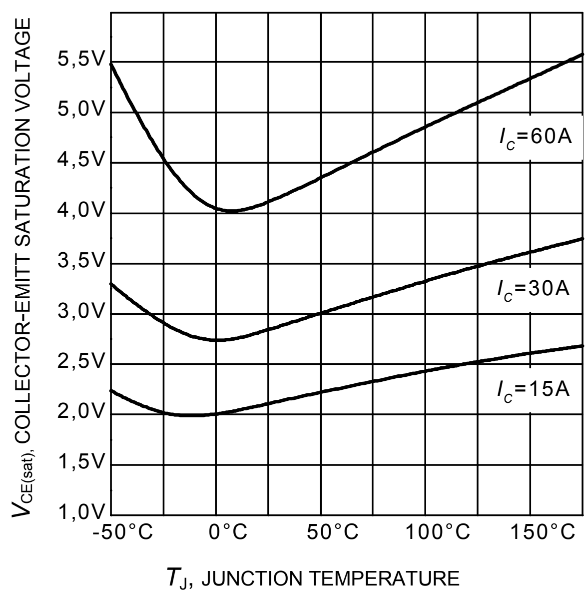


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
(V_{GE} = 15V)

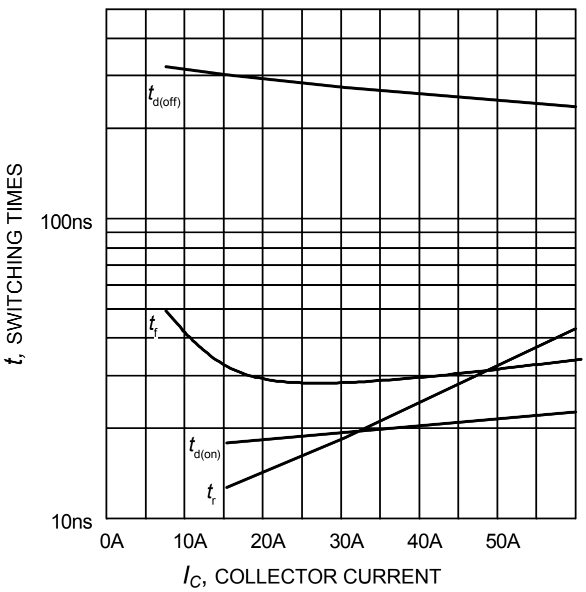


Figure 9. Typical switching times as a function of collector current
(inductive load, T_J=150°C, V_{CE}=400V, V_{GE}=0/15V, R_G=11Ω, Dynamic test circuit in Figure E)

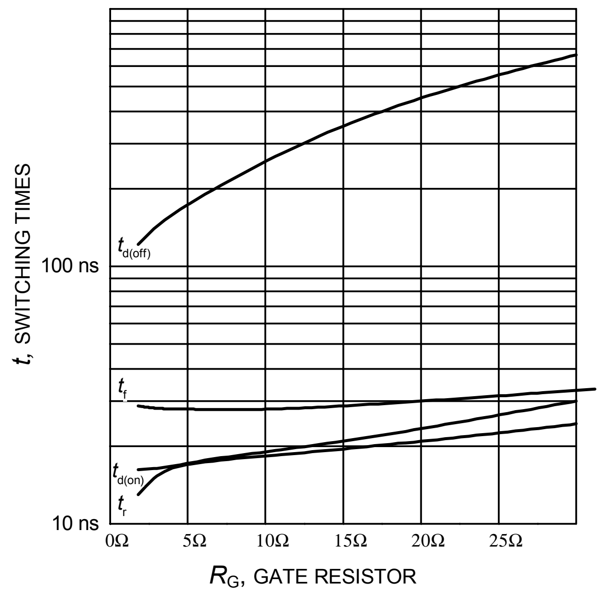


Figure 10. Typical switching times as a function of gate resistor
(inductive load, T_J=150°C, V_{CE}=400V, V_{GE}=0/15V, I_C=30A, Dynamic test circuit in Figure E)

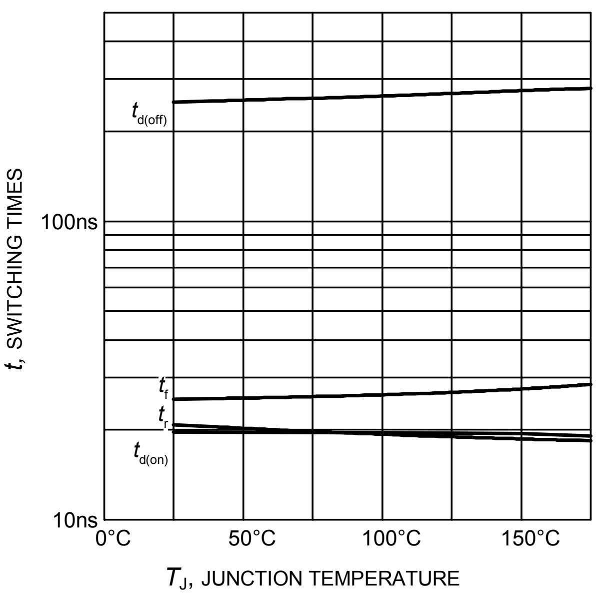


Figure 11. Typical switching times as a function of junction temperature
(inductive load, V_{CE}=400V, V_{GE}=0/15V, I_C=30A, R_G=11Ω, Dynamic test circuit in Figure E)

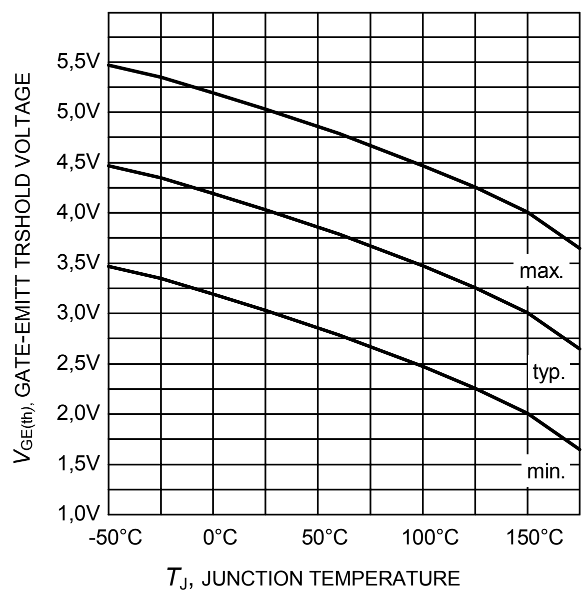


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
(I_C = 0.7mA)

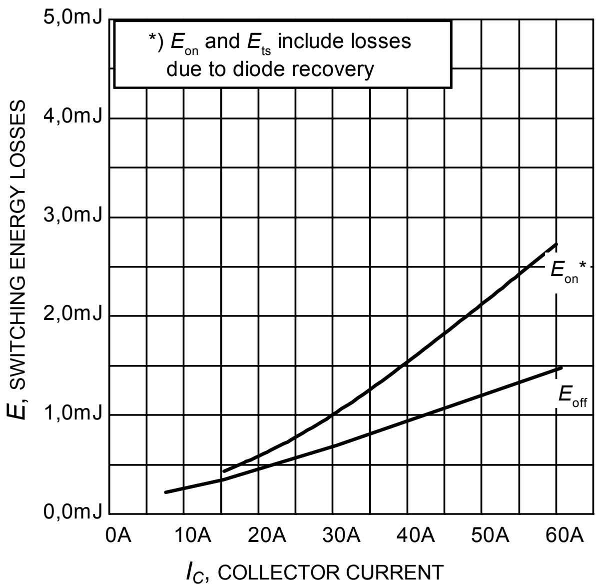


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, T_J=150°C, V_{CE}=400V, V_{GE}=0/15V, R_G=11Ω, Dynamic test circuit in Figure E)

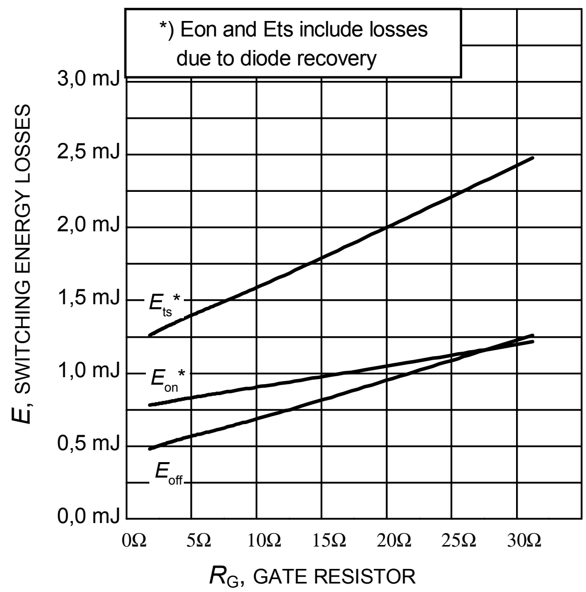


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, T_J=150°C, V_{CE}=400V, V_{GE}=0/15V, I_C=30A, Dynamic test circuit in Figure E)

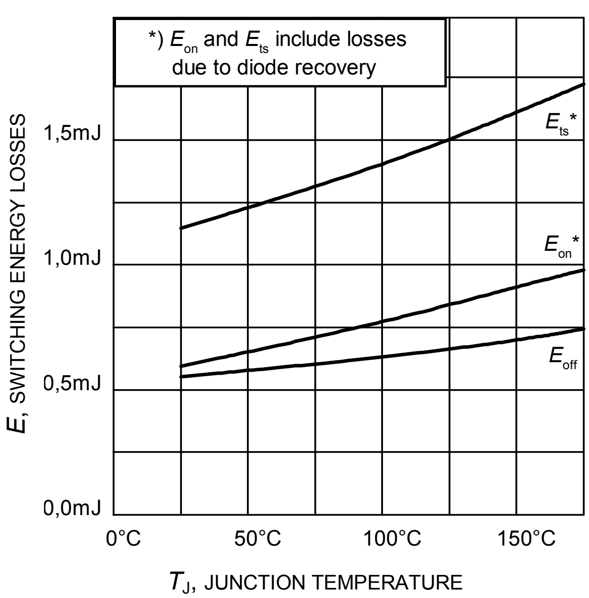


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, V_{CE}=400V, V_{GE}=0/15V, I_C=30A, R_G=11Ω, Dynamic test circuit in Figure E)

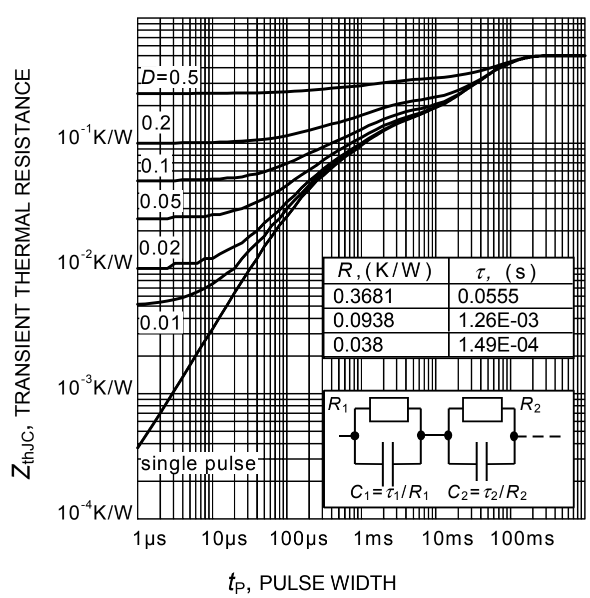


Figure 16. IGBT transient thermal resistance
($D = t_p / T$)

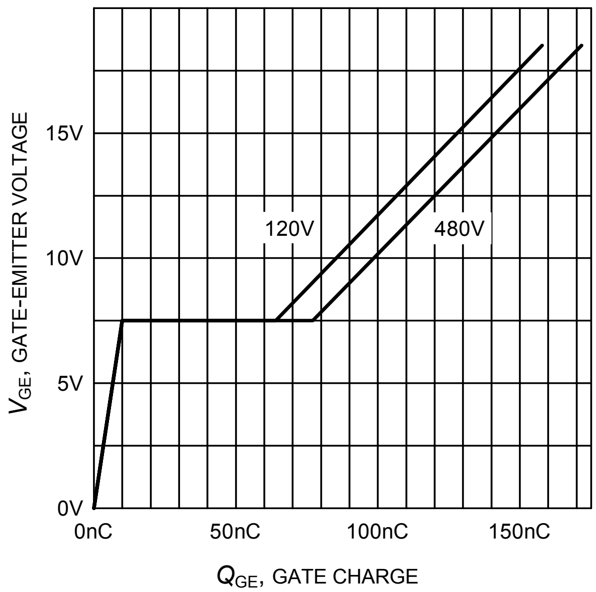


Figure 17. Typical gate charge
(I_C=30 A)

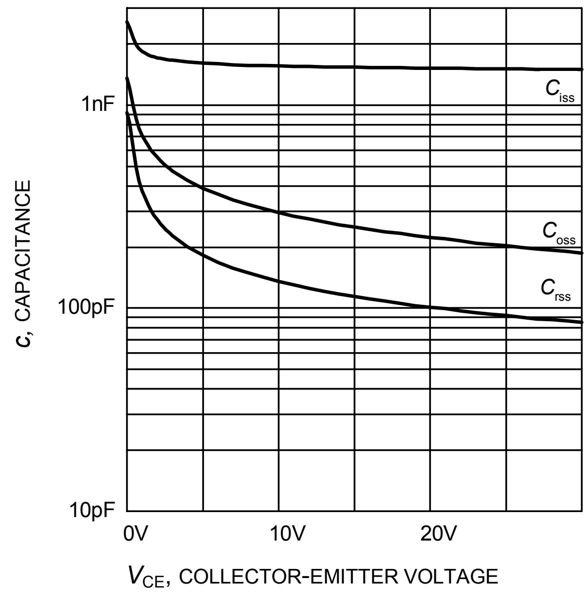


Figure 18. Typical capacitance as a function of collector-emitter voltage
(V_{GE}=0V, f = 1 MHz)

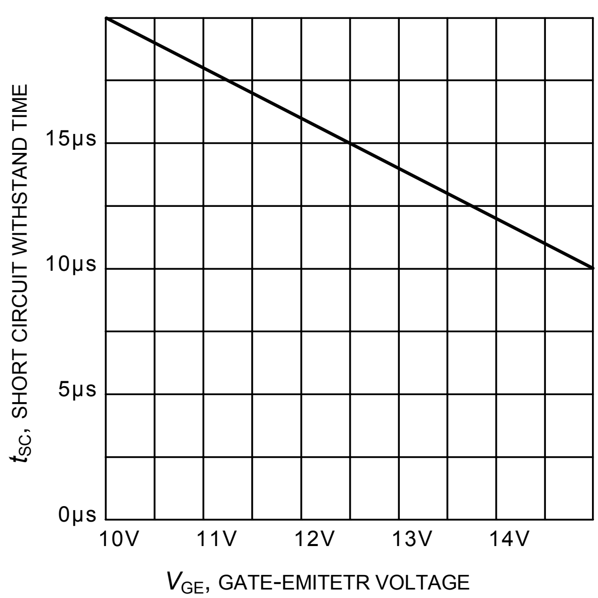


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
(V_{CE}=600V, start at T_J=25°C)

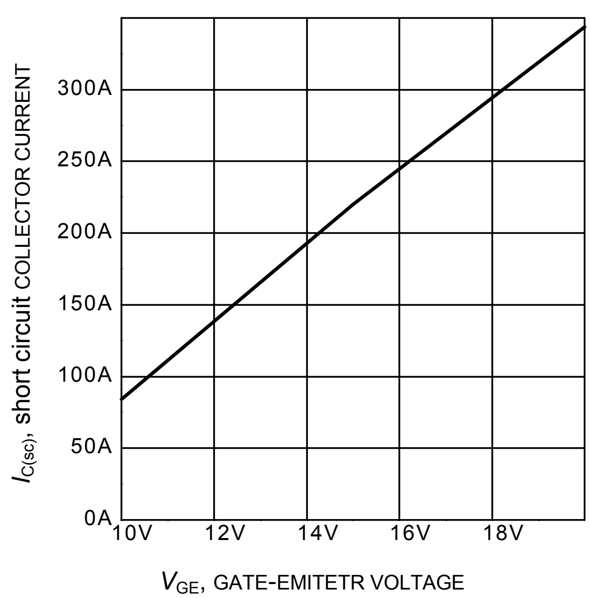


Figure 20. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq 600V$, $T_j \leq 150°C$)

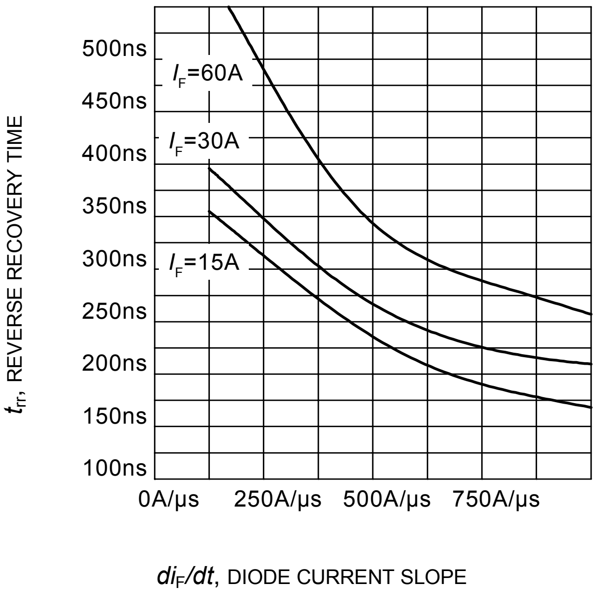


Figure 21. Typical reverse recovery time as a function of diode current slope
(V_R=400V, T_J=150°C,
Dynamic test circuit in Figure E)

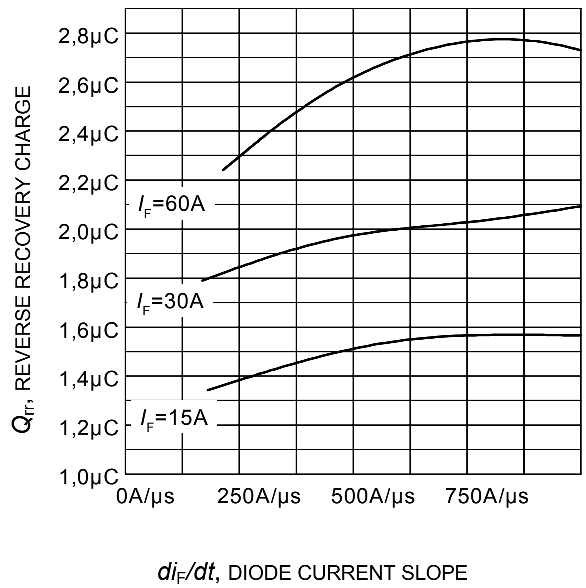


Figure 22. Typical reverse recovery charge as a function of diode current slope
(V_R=400V, T_J=150°C,
Dynamic test circuit in Figure E)

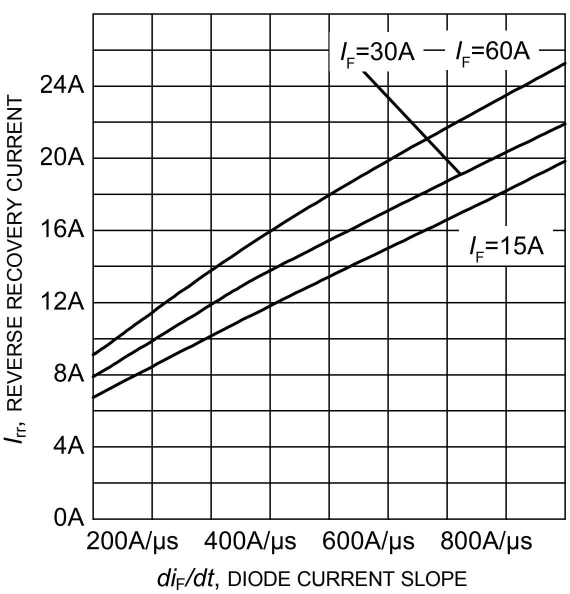


Figure 23. Typical reverse recovery current as a function of diode current slope
(V_R=400V, T_J=150°C,
Dynamic test circuit in Figure E)

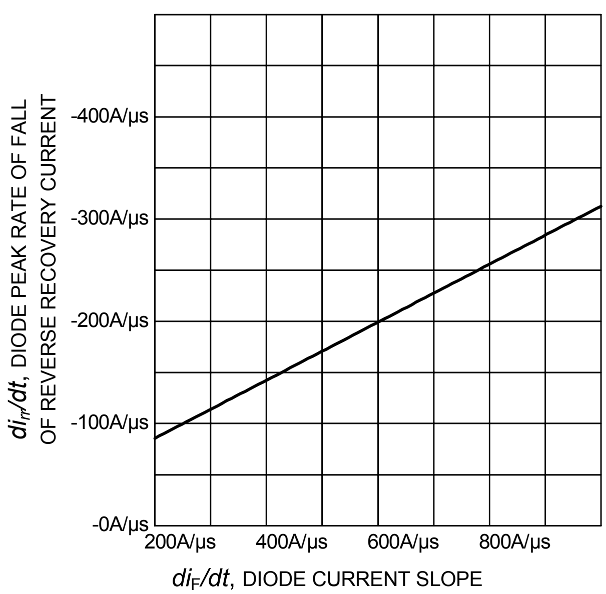


Figure 24. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope
(V_R=400V, T_J=150°C,
Dynamic test circuit in Figure E)

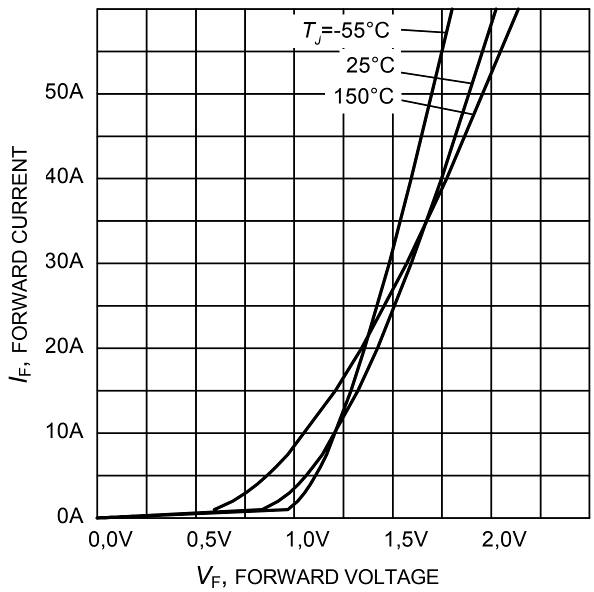


Figure 25. Typical diode forward current as a function of forward voltage

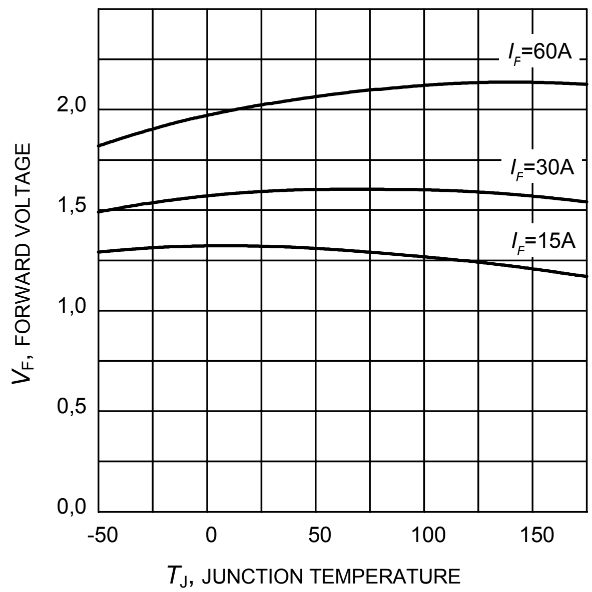


Figure 26. Typical diode forward voltage as a function of junction temperature

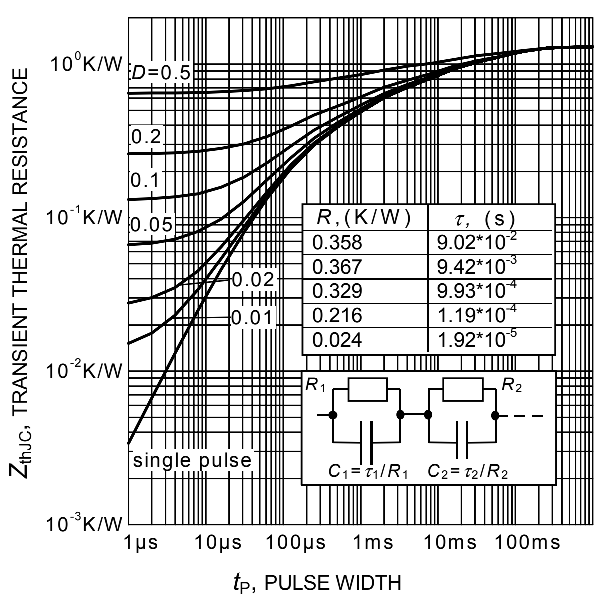
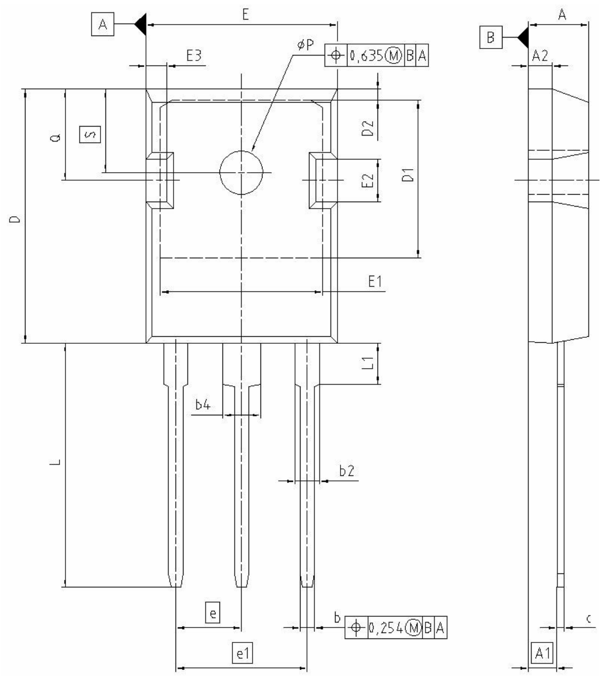


Figure 27. Diode transient thermal impedance as a function of pulse width
($D=t_P/T$)

PG-TO247-3-21



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.903	5.157	0.193	0.203
A1	2.273	2.527	0.092	0.096
A2	1.853	2.107	0.075	0.081
b	1.073	1.327	0.047	0.052
b2	1.903	2.386	0.075	0.094
b4	2.870	3.454	0.113	0.136
c	0.549	0.752	0.024	0.030
D	20.823	21.077	0.820	0.830
D1	17.323	17.831	0.682	0.702
D2	1.063	1.317	0.042	0.052
E	15.773	16.027	0.621	0.631
E1	13.893	14.147	0.547	0.557
E2	3.683	3.937	0.145	0.155
E3	1.683	1.937	0.066	0.076
e	5.450		0.215	
e1	10.900		0.430	
N	3		3	
L	20.053	20.307	0.789	0.799
L1	4.168	4.472	0.164	0.176
øP	3.559	3.661	0.140	0.144
Q	5.493	5.747	0.216	0.226
S	6.043	6.297	0.238	0.248

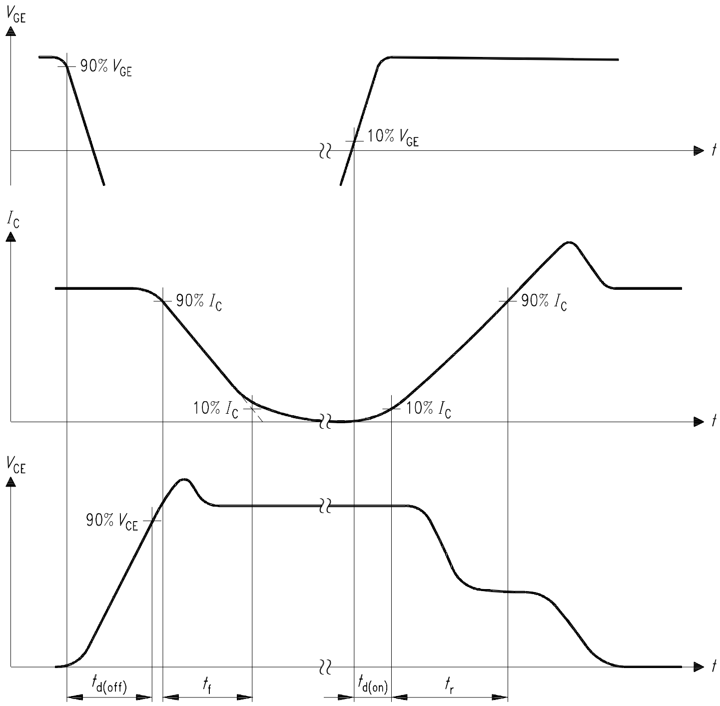


Figure A. Definition of switching times

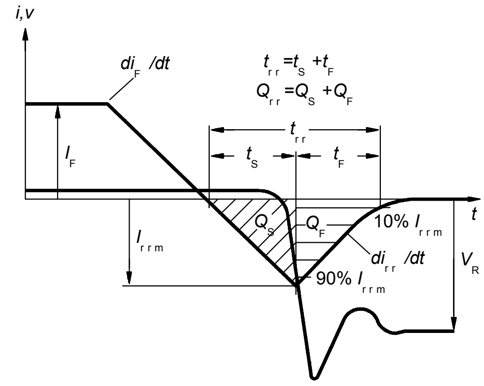


Figure C. Definition of diodes switching characteristics

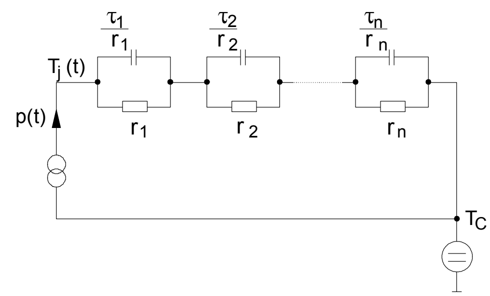


Figure D. Thermal equivalent circuit

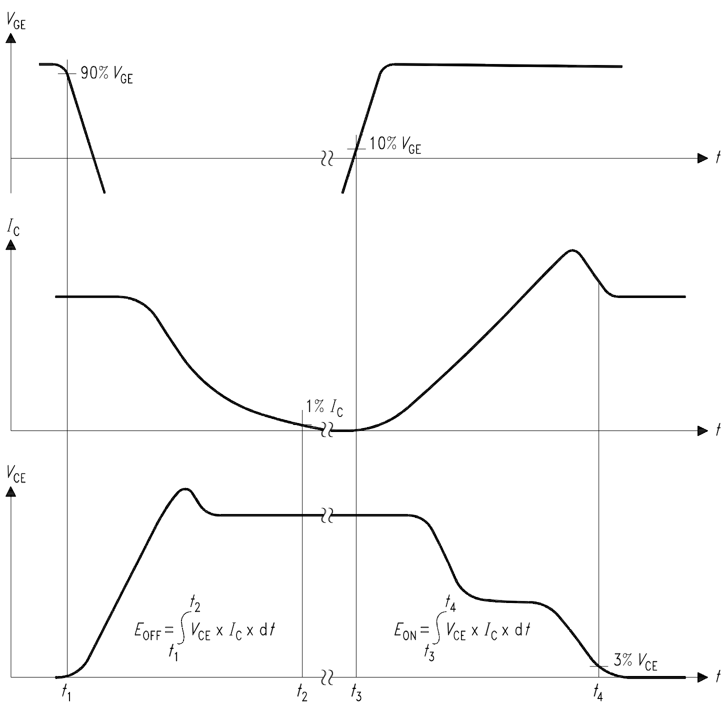


Figure B. Definition of switching losses

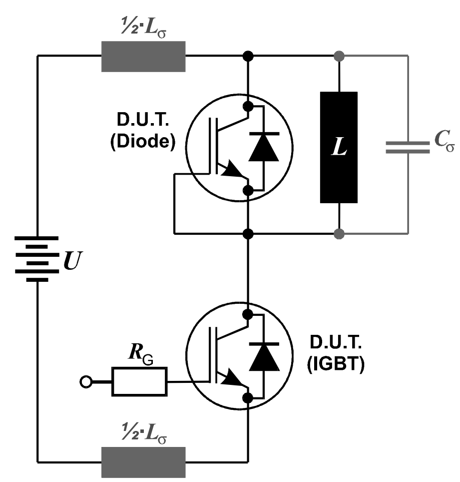


Figure E. Dynamic test circuit

Leakage inductance L_{σ} =60nH

and Stray capacity C_{σ} =40pF.

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